



## APPENDIX

**IN THE CLAIMS:**

Please cancel claims 18 and 19 without prejudice or disclaimer.

Please amend claims 1, 14 and 15 as follows:

1. (Amended) A semiconductor device comprising:

a substrate;

a source/drain diffused layer formed in the substrate for a transistor; and

a dummy diffused layer formed in the substrate,

wherein the source/drain diffused layer has its surface silicided, and

wherein the dummy diffused layer has its surface covered with an anti-silicidation

film at least partially, on which no gate electrode is provided.

112,1st (13) is a gate --  
See fig. 4B

14. (Amended) A semiconductor device comprising:

a substrate;

a source/drain diffused layer formed in the substrate for a transistor; and

a dummy diffused layer formed in the substrate,

wherein the source/drain diffused layer has its surface silicided, and

wherein the dummy diffused layer has its surface covered with an anti-silicidation

film at least partially, and

[The device of claim 1, ]wherein the dummy diffused layer is located between [a] an  
analog circuit block and [another] a digital circuit block.

RECEIVED  
APR -1 2003  
TECHNOLOGY CENTER 2800

15. (Amended) A semiconductor device comprising:  
a substrate;  
a source/drain diffused layer formed in the substrate for a transistor; and  
a dummy diffused layer formed in the substrate,  
wherein the source/drain diffused layer has its surface silicided, and  
wherein the dummy diffused layer has its surface covered with an anti-silicidation  
film at least partially, and

[The device of claim 1,] wherein the dummy diffused layer is not electrically coupled to another component via an interconnect.